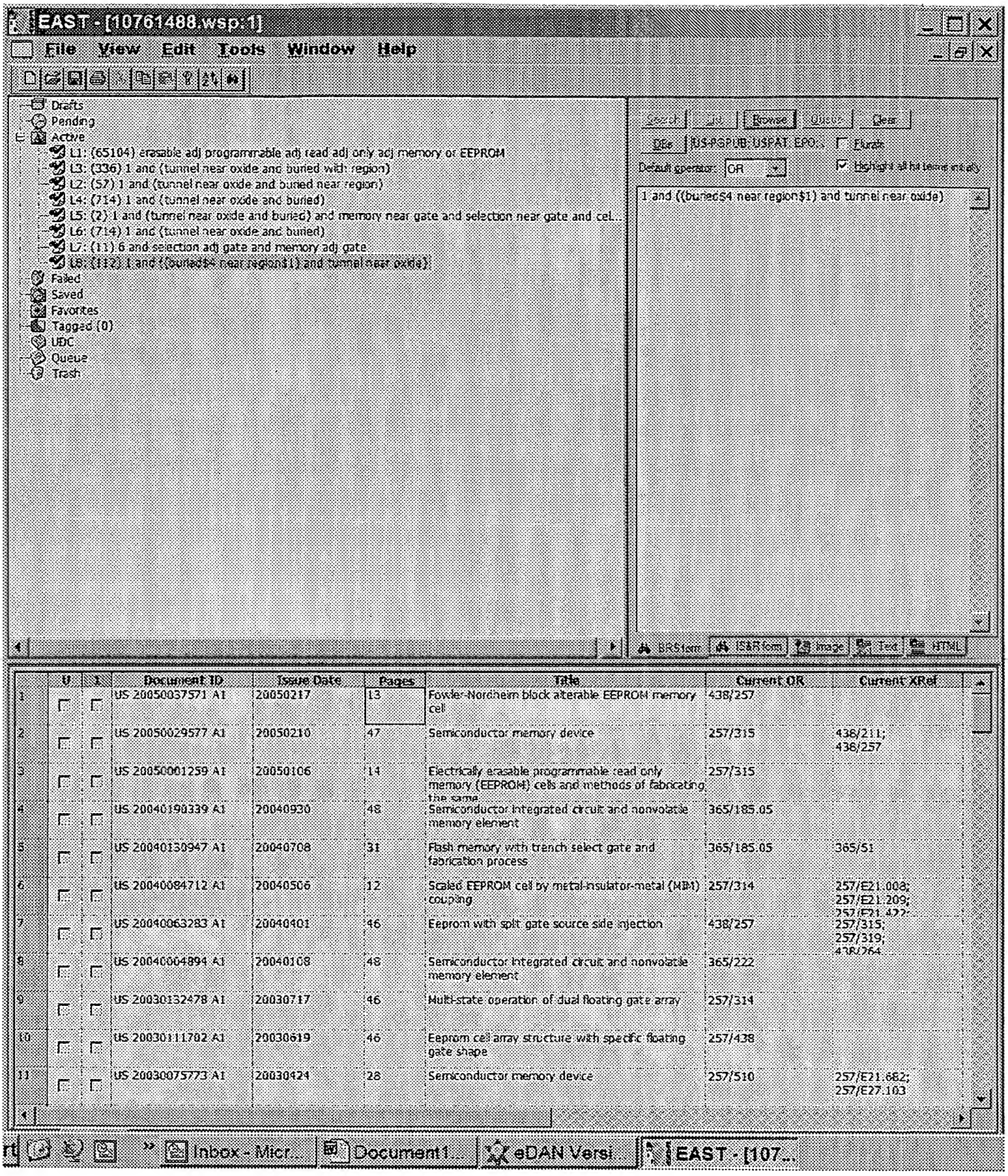

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1			US 20050037571 A1	20050217	13	Fowler-Nordheim block alterable EEPROM memory cell	438/257	
2			US 20050029577 A1	20050210	47	Semiconductor memory device	257/315	438/211; 438/257
3			US 20050001259 A1	20050106	14	Electrically erasable programmable read only memory (EEPROM) cells and methods of fabricating the same	257/315	
4			US 20040190339 A1	20040930	48	Semiconductor integrated circuit and nonvolatile memory element	365/185.05	
5			US 20040130947 A1	20040708	31	Flash memory with trench select gate and fabrication process	365/185.05	365/51
6			US 20040084712 A1	20040506	12	Scaled EEPROM cell by metal-insulator-metal (MIM) coupling	257/314	257/E21.008; 257/E21.209; 257/E21.422
7			US 20040063283 A1	20040401	46	Eeprom with split gate source side injection	438/257	257/315; 257/319; 438/264
8			US 20040004894 A1	20040108	48	Semiconductor integrated circuit and nonvolatile memory element	365/222	
9			US 20030132478 A1	20030717	46	Multi-state operation of dual floating gate array	257/314	
10			US 20030111702 A1	20030619	46	Eeprom cell array structure with specific floating gate shape	257/438	
11			US 20030075773 A1	20030424	28	Semiconductor memory device	257/510	257/E21.682; 257/E27.103